

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI PTB32003X** is Designed for Common Base General purpose amplifier Applications up to 4.2 GHz.

FEATURES INCLUDE:

- Diffused Emitter Ballasting Resistor
- Hermetic Flange Package
- Gold Metelization

MAXIMUM RATINGS

I_C	500 mA
V_{CB0}	40 V
P_{DISS}	7.6 W @ T _C = 75 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	12 °C/W

PACKAGE STYLE .250 2L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E		.125 / 3.18
F	.110 / 2.79	.117 / 2.97
G		.117 / 2.97
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 2.0 mA			40			V
BV_{CES}	I _C = 10 mA			40			V
I_{CB0}	V _{CE} = 24 V					20	μA
I_{EBO}	V _{EB} = 1.5 V					0.4	μA
C_{cb}	V _{CB} = 24 V	V _{EB} = 1.5 V	f = 1.0 MHz		3.0		pF
C_{ce}	V _{CB} = 24 V	V _{EB} = 1.5 V	f = 1.0 MHz		0.6		pF
P_{OUT}	V _{CC} = 24 V f = 3.0 GHz			2.5			W
η_C				35			%
G_P				8.0			dB